

Appl. No. 10/761,702
Examiner: Warren, Matthew E, Art Unit 2815
In response to the Office Action dated June 30, 2006

Date: September 30, 2006
Attorney Docket No. 10113671

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claim 1 (currently amended): A bit line contact structure of a memory device, comprising:
a substrate having a transistor of the memory device thereon, the transistor having a raised gate electrode, a drain region, and a source region;
a composite dielectric layer, sequentially having a first dielectric layer, barrier layer, and second dielectric layer, directly on the transistor, the first dielectric layer comprising polyimide, the composite dielectric layer having an opening exposing the drain region; and
a tungsten layer or a polysilicon layer [[in]] filling the opening,
wherein the thickness of the first dielectric layer is thicker than the second dielectric layer.

Claim 2 (canceled)

Claim 3 (original): The structure as claimed in claim 1, wherein the first dielectric layer is about 3000Å to 4000Å thick.

Claim 4 (original): The structure as claimed in claim 1, wherein the barrier layer is SiN.

Claim 5 (original): The structure as claimed in claim 1, wherein the barrier layer is about 100Å to 300Å thick.

Claim 6 (original): The structure as claimed in claim 1, wherein the second dielectric layer comprises an oxide layer.

Claim 7 (original): The structure as claimed in claim 1, wherein the second dielectric layer is about 1000Å to 3000Å thick.

Claim 8 (canceled)

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Claim 9 (currently amended): The structure as claimed in claim 1, wherein the ~~first conductive~~
the tungsten layer or polysilicon layer is about 2000Å to 4000Å thick.

Claims 10-26 (canceled)

Claim 27 (previously presented): The structure as claimed in claim 1, wherein the polyimide is
fluorinated polyimide.

Claim 28 (previously presented): The structure as claimed in claim 1, wherein the first dielectric
layer comprises polysilsequioxane.